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INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Docket Number (Optional)	Application Number
BUR920000029[redacted]1	09/713,830
Applicant(s) Furukawa et al.	
Filing Date 11/15/2000	**Group Art Unit** 2826

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
KL	AA	5,650,342	7/22/1997	Satoh et al.	437	36	Oct 30, 1992
KL	AB	5,650,343	7/22/1997	Luning et al.	437	36	Jun 7, 1995
KL	AC	6,037,630	3/14/2000	Igarashi et al.	257	336	Nov 21, 1997

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FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation YES	Translation NO
[redacted]	AD	JP10294453A2	04/17/1997	Japan	H01L	29/78	✓	
[redacted]	AE	WO 00/57461	09/28/2000	France	H01L	21/28		✓

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OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*

KL	AF	"Well-controlled, selectively under-etched Si/SiGe gates for RF and high performance CMOS" T. Skotnicki et al., 2000 Symposium on VLSI Technology Digest of Technical Papers, 2000 IEEE, pp. 156-157
KL	AG	PCT International Search Report

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EXAMINER	DATE CONSIDERED
Kevin Quinto	12/22/02

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.